

Luigi Mariucci

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8077467/publications.pdf>

Version: 2024-02-01

181
papers

2,502
citations

185998

28
h-index

301761

39
g-index

181
all docs

181
docs citations

181
times ranked

1814
citing authors

#	ARTICLE	IF	CITATIONS
1	Effects of illumination on the electrical characteristics in organic thin-film transistors based on dinaphtho [2,3-b:2',3'-f] thieno[3,2-b] thiophene (DNTT): Experiment and modeling. Synthetic Metals, 2022, 2.1 283, 116985.		2
2	Highly sensitive organic phototransistor for flexible optical detector arrays. Organic Electronics, 2022, 102, 106452.	1.4	13
3	Historical evolution of pulsed laser annealing for semiconductor processing. , 2021, , 1-48.		0
4	Hybrid Electrothermal Simulations of GaN HEMT Devices Based on Self-Heating Free Virtual Electrical Characteristics. IEEE Transactions on Electron Devices, 2021, 68, 3740-3747.	1.6	6
5	Electrical instability in short channel organic thin-film transistors induced by lucky-polaron mechanism. Organic Electronics, 2021, 98, 106279.	1.4	1
6	Three-dimensional characterization of OTFT on modified hydrophobic flexible polymeric substrate by low energy Cs+ ion sputtering. Applied Surface Science, 2018, 448, 628-635.	3.1	15
7	Staggered top-gate PDIF-CN2 N-type thin film transistors on flexible plastic substrates. Organic Electronics, 2018, 57, 226-231.	1.4	2
8	Gravure printed organic thin film transistors: Study on the ink printability improvement. Organic Electronics, 2018, 61, 104-112.	1.4	15
9	A DC and small signal AC model for organic thin film transistors including contact effects and non quasi static regime. Organic Electronics, 2017, 41, 345-354.	1.4	16
10	Logic gates and memory elements design and simulation using PMOS organic transistor. , 2017, , .		1
11	A large signal non quasi static model of printed organic TFTs and simulation of CMOS circuits. , 2017, , .		7
12	Growth and Manipulation of Organic Semiconductors Microcrystals by Wet Lithography. Advanced Functional Materials, 2016, 26, 2387-2393.	7.8	4
13	A Compact SPICE Model for Organic TFTs and Applications to Logic Circuit Design. IEEE Nanotechnology Magazine, 2016, 15, 754-761.	1.1	16
14	Contact Effects in Organic Thin-Film Transistors: Device Physics and Modeling. , 2016, , 945-969.		1
15	A large signal non quasi static compact model for printed organic thin film transistors. , 2016, , .		2
16	Investigation of Gate Direct-Current and Fluctuations in Organic p-Type Thin-Film Transistors. IEEE Electron Device Letters, 2016, 37, 1625-1627.	2.2	0
17	The Role of Defective Regions Near the Contacts on the Electrical Characteristics of Bottom-Gate Bottom-Contact Organic TFTs. Journal of Display Technology, 2016, 12, 252-257.	1.3	8
18	Correlated Mobility Fluctuations and Contact Effects in p-Type Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2016, 63, 1239-1245.	1.6	11

#	ARTICLE	IF	CITATIONS
19	Graphene-based field effect transistors for radiation-induced field sensing. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2016, 824, 392-393.	0.7	3
20	Contact Effects in Organic Thin-Film Transistors: Device Physics and Modeling. , 2016, , 1-25.		0
21	Water stable organic thin film transistors (TFTs) made on flexible substrates. , 2015, , .		1
22	A compact Spice model for organic TFTs and applications to logic circuit design. , 2015, , .		6
23	Unified drain-current model of complementary p- and n-type OTFTs. Organic Electronics, 2015, 22, 5-11.	1.4	34
24	Evidence of Correlated Mobility Fluctuations in p-Type Organic Thin-Film Transistors. IEEE Electron Device Letters, 2015, 36, 390-392.	2.2	17
25	Modeling of Capacitance Characteristics of Printed p-Type Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2014, 61, 4120-4127.	1.6	15
26	Contact Effects in Amorphous InGaZnO Thin Film Transistors. Journal of Display Technology, 2014, 10, 956-961.	1.3	25
27	Fully-organic flexible tactile sensor for advanced robotic applications. , 2014, , .		5
28	(Invited) Contact Effects in Organic Thin Film Transistors with Different Device Structures. ECS Transactions, 2014, 64, 131-142.	0.3	3
29	Variation-based design of an AM demodulator in a printed complementary organic technology. Organic Electronics, 2014, 15, 904-912.	1.4	34
30	Principle of operation and modeling of source-gated transistors. Journal of Applied Physics, 2013, 114, .	1.1	35
31	Analysis of Kink Effect and Short Channel Effects in Fully Self-Aligned Gate Overlapped Lightly Doped Drain Polysilicon TFTs. Journal of Display Technology, 2013, 9, 764-769.	1.3	6
32	(Invited) Contact Effects in Organic and Inorganic Thin Film Transistors. ECS Transactions, 2013, 54, 171-185.	0.3	1
33	High performance printed N and P-type OTFTs enabling digital and analog complementary circuits on flexible plastic substrate. Solid-State Electronics, 2013, 84, 167-178.	0.8	72
34	Current spreading effects in fully printed p-channel organic thin film transistors with Schottky source-drain contacts. Organic Electronics, 2013, 14, 86-93.	1.4	44
35	(Invited) Printed Organic TFTs on Flexible Substrate for Complementary Circuits. ECS Transactions, 2013, 54, 153-163.	0.3	0
36	Self-heating effects on the electrical instability of fully printed p-type organic thin film transistors. Applied Physics Letters, 2012, 101, .	1.5	13

#	ARTICLE	IF	CITATIONS
37	Flexible PVDF-TrFE Pyroelectric Sensor Integrated on a Fully Printed P-channel Organic Transistor. <i>Procedia Engineering</i> , 2012, 47, 526-529.	1.2	5
38	Reduction of Short Channel Effects and Hot Carrier Induced Instability in Fully Self-Aligned Gate Overlapped Lightly Doped Drain Polysilicon TFTs. <i>Journal of Display Technology</i> , 2012, 8, 18-22.	1.3	5
39	High performance printed N and P-type OTFTs for complementary circuits on plastic substrate. , 2012, , .		18
40	Design of analog and digital building blocks in a fully printed complementary organic technology. , 2012, , .		14
41	Analysis of contact effects in fully printed p-channel organic thin film transistors. <i>Organic Electronics</i> , 2012, 13, 2017-2027.	1.4	33
42	Edge Effects in Self-Heating-Related Instabilities in p-Channel Polycrystalline-Silicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2011, 32, 1707-1709.	2.2	2
43	Carbon nanotube semitransparent electrodes for amorphous silicon based photovoltaic devices. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	34
44	Giant and reversible enhancement of the electrical resistance of GaAs $1\hat{\sim}xNx$ by hydrogen irradiation. <i>Physical Review B</i> , 2011, 84, .	1.1	10
45	Pentacene thin film transistors with (polytetrafluoroethylene) PTFE-like encapsulation layer. <i>Organic Electronics</i> , 2011, 12, 119-124.	1.4	16
46	Influence of structural properties on environmental stability of pentacene thin film transistors. <i>Organic Electronics</i> , 2011, 12, 447-452.	1.4	19
47	Contact effects in high performance fully printed p-channel organic thin film transistors. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	60
48	Downscaling effects on self-heating related instabilities in p-channel polycrystalline silicon thin film transistors. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	6
49	(Invited) Short Channel Effects and Drain Field Relief Architectures in Polysilicon TFTs. <i>ECS Transactions</i> , 2011, 37, 3-14.	0.3	2
50	Threshold voltage in short channel polycrystalline silicon thin film transistors: Influence of drain induced barrier lowering and floating body effects. <i>Journal of Applied Physics</i> , 2010, 107, .	1.1	20
51	(Invited) Downscaling Issues in Polycrystalline Silicon TFTs. <i>ECS Transactions</i> , 2010, 33, 3-22.	0.3	3
52	Quantum confinement effects in hydrogen-intercalated Ga $1\hat{\sim}xAsxNx$ -GaAs $1\hat{\sim}xNx$:H planar heterostructures investigated by photoluminescence spectroscopy. <i>Physical Review B</i> , 2010, 81, .	1.1	8
53	Low-temperature, self-catalyzed growth of Si nanowires. <i>Nanotechnology</i> , 2010, 21, 255601.	1.3	22
54	Analysis of Self-Heating-Related Instability in Self-Aligned p-Channel Polycrystalline-Silicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2010, 31, 830-832.	2.2	17

#	ARTICLE	IF	CITATIONS
55	Light polarization control in strain-engineered GaAsN/GaAsN:H heterostructures. Applied Physics Letters, 2009, 94, 261905.	1.5	19
56	Role of gate oxide thickness in controlling short channel effects in polycrystalline silicon thin film transistors. Applied Physics Letters, 2009, 95, .	1.5	11
57	Effective channel length and parasitic resistance determination in non self-aligned low temperature polycrystalline silicon thin film transistors. Thin Solid Films, 2009, 517, 6353-6357.	0.8	8
58	Pentacene TFTs with parylene passivation layer. Thin Solid Films, 2009, 517, 6283-6286.	0.8	31
59	Negative biasâ€“temperature stress in non-self-aligned p-channel polysilicon TFTs. Thin Solid Films, 2009, 517, 6379-6382.	0.8	6
60	Analysis of self-heating related instability in n-channel polysilicon thin film transistors fabricated on polyimide. Thin Solid Films, 2009, 517, 6371-6374.	0.8	24
61	Chemoresistive nanofibrous sensor array and read-out electronics on flexible substrate. , 2009, , .		1
62	Electrical instability in self-aligned p-channel polysilicon TFTs related to damaged regions present at the gate edges. Solid-State Electronics, 2008, 52, 406-411.	0.8	3
63	Effect of active layer thickness on electrical characteristics of pentacene TFTs with PMMA buffer layer. Solid-State Electronics, 2008, 52, 412-416.	0.8	27
64	Low-temperature polysilicon thin film transistors on polyimide substrates for electronics on plastic. Solid-State Electronics, 2008, 52, 348-352.	0.8	122
65	Interdigitated sensorial system on flexible substrate. , 2008, , .		7
66	Effect of hydrogen incorporation temperature in plane-engineered GaAsNâˆ•GaAsN:H heterostructures. Applied Physics Letters, 2008, 92, 221901.	1.5	14
67	In-plane band gap modulation investigated by secondary electron imaging of GaAsN/GaAsN:H heterostructures. Applied Physics Letters, 2008, 93, 102116.	1.5	9
68	Low-Temperature Annealing Combined with Laser Crystallization for Polycrystalline Silicon TFTs on Polymeric Substrate. Journal of the Electrochemical Society, 2008, 155, H764.	1.3	21
69	â€œHumpâ€“characteristics and edge effects in polysilicon thin film transistors. Journal of Applied Physics, 2008, 104, .	1.1	54
70	Role of field enhanced mechanisms and impact ionization on the threshold voltage of short channel polycrystalline silicon thin film transistors. Applied Physics Letters, 2008, 93, 193512.	1.5	6
71	Grain Boundary Characterisation in Sequentially Laterally Solidified Polycrystalline-Silicon Thin Film Transistors. ECS Transactions, 2007, 8, 211-216.	0.3	0
72	Hot Carrier Effects in p-Channel Polycrystalline Silicon Thin Film Transistors Fabricated on Flexible Substrates. Japanese Journal of Applied Physics, 2007, 46, 1299-1302.	0.8	4

#	ARTICLE	IF	CITATIONS
73	Excimer Laser Annealing for Low-Temperature Polysilicon Thin Film Transistor Fabrication on Plastic Substrates. , 2007, , .		2
74	Hydrogen-induced Nitrogen Passivation in Dilute Nitrides: A Novel Approach to Defect Engineering. Materials Research Society Symposia Proceedings, 2007, 994, 1.	0.1	0
75	In-Plane Band Gap Engineering by Hydrogenation of Dilute Nitride Semiconductors. AIP Conference Proceedings, 2007, , .	0.3	0
76	Grain boundary evaluation in sequentially laterally solidified polycrystalline-silicon devices. Journal of Applied Physics, 2007, 101, 094502.	1.1	12
77	Excimer Laser Annealing of Ion-Implanted Silicon: Dopant Activation, Diffusion and Defect Formation. , 2007, , .		0
78	Aging effects and electrical stability in pentacene thin film transistors. Thin Solid Films, 2007, 515, 7546-7550.	0.8	31
79	Insight into excimer laser crystallization exploiting ellipsometry: Effect of silicon film precursor. Thin Solid Films, 2007, 515, 7508-7512.	0.8	4
80	Electrical stability in self-aligned p-channel polysilicon thin film transistors. Thin Solid Films, 2007, 515, 7571-7575.	0.8	14
81	Modelling velocity saturation and kink effects in p-channel polysilicon thin-film transistors. Thin Solid Films, 2007, 515, 7417-7421.	0.8	8
82	RBS-channeling analysis of ion-irradiation effects in heavily-doped Si:As. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 253-256.	0.6	1
83	Integration of Melting Excimer Laser Annealing in Power MOS Technology. IEEE Transactions on Electron Devices, 2007, 54, 852-860.	1.6	13
84	Asymmetric fingered polysilicon p-channel thin film transistor structure for kink effect suppression. Thin Solid Films, 2007, 515, 7433-7436.	0.8	2
85	Very High Performance GaN HEMT devices by Optimized Buffer and Field Plate Technology. , 2006, , .		4
86	Annealing temperature effects on the electrical characteristics of p-channel polysilicon thin film transistors. Journal of Non-Crystalline Solids, 2006, 352, 1723-1727.	1.5	3
87	Analysis of electrical characteristics of high performance pentacene thin-film transistors with PMMA buffer layer. Journal of Non-Crystalline Solids, 2006, 352, 1765-1768.	1.5	15
88	Ultra-shallow junction by laser annealing: Integration issues and modelling. Nuclear Instruments & Methods in Physics Research B, 2006, 253, 1-8.	0.6	2
89	Excimer Laser annealing for shallow junction formation in Si power MOS devices. Thin Solid Films, 2006, 504, 2-6.	0.8	15
90	Hot-carrier-induced degradation of LDD polysilicon TFTs. IEEE Transactions on Electron Devices, 2006, 53, 43-50.	1.6	21

#	ARTICLE	IF	CITATIONS
91	Numerical simulation of parasitic resistance effects in polycrystalline silicon TFTs. IEEE Transactions on Electron Devices, 2006, 53, 573-577.	1.6	10
92	Fabrication and nonlinear characterization of GaN HEMTs on SiC and sapphire for high-power applications. International Journal of RF and Microwave Computer-Aided Engineering, 2006, 16, 70-80.	0.8	23
93	Effects of Fabrication Parameters on the Electrical Stability of Gate Overlapped Lightly Doped Drain Polysilicon Thin-Film Transistors. Japanese Journal of Applied Physics, 2006, 45, 4384-4388.	0.8	1
94	Modelling Velocity Saturation Effects in Polysilicon Thin-Film Transistors. Japanese Journal of Applied Physics, 2006, 45, 4374-4377.	0.8	6
95	Self-heating effects in polycrystalline silicon thin film transistors. Applied Physics Letters, 2006, 89, 093509.	1.5	20
96	Bragg reflector based gate stack architecture for process integration of excimer laser annealing. Applied Physics Letters, 2006, 89, 253502.	1.5	1
97	Controlling field-effect mobility in pentacene-based transistors by supersonic molecular-beam deposition. Applied Physics Letters, 2006, 88, 132106.	1.5	39
98	Improved electrical stability in asymmetric fingered polysilicon thin film transistors. Applied Physics Letters, 2006, 89, 123506.	1.5	5
99	Hot-carrier effects in p-channel polycrystalline silicon thin film transistors. Applied Physics Letters, 2006, 89, 183518.	1.5	9
100	Aging effects in pentacene thin-film transistors: Analysis of the density of states modification. Applied Physics Letters, 2006, 88, 193508.	1.5	48
101	Silicon dioxide deposited by ECR-PECVD for low-temperature Si devices processing. Microelectronics Reliability, 2005, 45, 879-882.	0.9	2
102	Boron distribution in silicon after excimer laser annealing with multiple pulses. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 228-231.	1.7	2
103	Excimer laser annealing of B and BF ₂ implanted Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 232-234.	1.7	3
104	Short channel effects in polysilicon thin film transistors. Thin Solid Films, 2005, 487, 221-226.	0.8	26
105	Stable p-channel polysilicon thin film transistors fabricated by laser doping technique. Thin Solid Films, 2005, 487, 232-236.	0.8	12
106	Improved electrical stability in asymmetric fingered polysilicon thin film transistors. Thin Solid Films, 2005, 487, 237-241.	0.8	3
107	Channel doping effects in poly-Si thin film transistors. Thin Solid Films, 2005, 487, 242-246.	0.8	4
108	The effect of excimer laser pretreatment on diffusion and activation of boron implanted in silicon. Applied Physics Letters, 2005, 87, 192109.	1.5	15

#	ARTICLE	IF	CITATIONS
109	Enhanced boron diffusion in excimer laser preannealed Si. Applied Physics Letters, 2005, 86, 151902.	1.5	9
110	Depth distribution of B implanted in Si after excimer laser irradiation. Applied Physics Letters, 2005, 86, 051909.	1.5	29
111	Boron distribution in silicon after multiple pulse excimer laser annealing. Applied Physics Letters, 2005, 87, 081901.	1.5	8
112	Electrical characterization of directionally solidified polycrystalline silicon. Journal of Applied Physics, 2005, 98, 033702.	1.1	7
113	Dopant and defect interactions in polycrystalline silicon thin-film transistors. Journal of Applied Physics, 2005, 97, 104515.	1.1	4
114	High-field-effect-mobility pentacene thin-film transistors with polymethylmetacrylate buffer layer. Applied Physics Letters, 2005, 86, 203505.	1.5	70
115	Material modifications induced by laser annealing in two-dimensional structures. Applied Physics Letters, 2004, 84, 4738-4740.	1.5	22
116	Kink effect in short-channel polycrystalline silicon thin-film transistors. Applied Physics Letters, 2004, 85, 3113-3115.	1.5	56
117	Polysilicon TFT Structures for Kink-Effect Suppression. IEEE Transactions on Electron Devices, 2004, 51, 1135-1142.	1.6	40
118	SuMBE based organic thin film transistors. Synthetic Metals, 2004, 146, 291-295.	2.1	12
119	Computational methods for the simulation of the excimer laser annealing in MOS technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 100-104.	1.7	0
120	Excimer laser annealing of shallow As and B doped layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 352-357.	1.7	3
121	Boron-enhanced diffusion in excimer laser annealed Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 114-117.	1.7	2
122	Electrical activation phenomena induced by excimer laser annealing in B-implanted silicon. Applied Physics Letters, 2004, 85, 2268-2270.	1.5	11
123	Analysis of electrical characteristics of gate overlapped lightly doped drain (GOLDD) polysilicon thin-film transistors with different LDD doping concentration. IEEE Transactions on Electron Devices, 2003, 50, 2425-2433.	1.6	28
124	A new self-consistent model for the analysis of hot-carrier induced degradation in lightly doped drain (LDD) and gate overlapped LDD polysilicon TFTs. Thin Solid Films, 2003, 427, 117-122.	0.8	11
125	Lateral growth control by thickness spatial modulation of amorphous silicon film. Thin Solid Films, 2003, 427, 314-318.	0.8	5
126	Observation of super lateral growth in long pulse (170 ns) excimer laser crystallization of a-Si films. Thin Solid Films, 2003, 427, 319-323.	0.8	6

#	ARTICLE	IF	CITATIONS
127	Crystallization mechanisms in laser irradiated thin amorphous silicon films. Thin Solid Films, 2003, 427, 91-95.	0.8	27
128	Noise performance of polycrystalline silicon thin-film transistors made by sequential lateral solidification. Applied Physics Letters, 2003, 82, 2709-2711.	1.5	5
129	Surface-scattering effects in polycrystalline silicon thin-film transistors. Applied Physics Letters, 2003, 82, 3119-3121.	1.5	43
130	Dopant redistribution and electrical activation in silicon following ultra-low energy boron implantation and excimer laser annealing. Physical Review B, 2003, 67, .	1.1	60
131	Comparative analysis of advanced poly-silicon thin-film transistor architectures for drain field relief. , 2003, 5004, 150.		1
132	Mechanisms of Dopant Redistribution and Retention in Silicon Following Ultra-low Energy Boron Implantation and Excimer Laser Annealing. , 2002, , .		0
133	Redistribution and electrical activation of ultralow energy implanted boron in silicon following laser annealing. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 644.	1.6	34
134	Hot carrier-induced degradation of gate overlapped lightly doped drain (GOLDD) polysilicon TFTs. IEEE Transactions on Electron Devices, 2002, 49, 636-642.	1.6	15
135	Ultra-shallow junction formation by excimer laser annealing and low energy (<1 keV) B implantation: A two-dimensional analysis. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 401-408.	0.6	36
136	A novel fabrication process for polysilicon thin film transistors with source/drain contacts formed by deposition and lift-off of highly doped layers. Solid-State Electronics, 2002, 46, 1351-1358.	0.8	17
137	Low-frequency excess noise induced by hot-carrier injection in polysilicon thin-film transistors. Thin Solid Films, 2001, 383, 147-150.	0.8	0
138	Advanced excimer laser crystallization techniques. Thin Solid Films, 2001, 383, 39-44.	0.8	22
139	Fabrication of ultra-shallow junctions with high electrical activation by excimer laser annealing. Materials Science in Semiconductor Processing, 2001, 4, 417-423.	1.9	13
140	Excimer laser crystallization techniques for polysilicon TFTs. Applied Surface Science, 2000, 154-155, 95-104.	3.1	18
141	Low-frequency noise in gate overlapped lightly doped drain polycrystalline silicon thin-film transistors. Applied Physics Letters, 2000, 76, 3268-3270.	1.5	5
142	Two-dimensional delineation of ultrashallow junctions obtained by ion implantation and excimer laser annealing. Applied Physics Letters, 2000, 77, 552-554.	1.5	33
143	TECHNOLOGY OF LARGE AREA TWO-DIMENSIONAL COLOR IMAGE SENSOR. , 2000, , .		0
144	Numerical Analysis of the Electrical Characteristics of Gate Overlapped Lightly Doped Drain Polysilicon Thin Film Transistors. Japanese Journal of Applied Physics, 1999, 38, 3475-3481.	0.8	16

#	ARTICLE	IF	CITATIONS
145	A Two-Pass Excimer Laser Annealing Process to Control Amorphous Silicon Crystallization. Japanese Journal of Applied Physics, 1999, 38, L907-L910.	0.8	22
146	Temperature dependence of the transfer characteristics of polysilicon thin film transistors fabricated by excimer laser crystallization. Journal of Applied Physics, 1999, 85, 616-618.	1.1	19
147	Lateral growth control in excimer laser crystallized polysilicon. Thin Solid Films, 1999, 337, 137-142.	0.8	39
148	Temperature analysis of polysilicon thin-film transistors made by excimer laser crystallization. Thin Solid Films, 1999, 337, 196-199.	0.8	5
149	Hot carrier effects in polycrystalline silicon thin-film transistors: analysis of electrical characteristics and noise performance modifications. Microelectronics Reliability, 1999, 39, 45-52.	0.9	9
150	Determination of excess current due to impact ionization in polycrystalline silicon thin-film transistors. Solid-State Electronics, 1998, 42, 613-618.	0.8	8
151	A Critical Assessment of Different Models of the Metastability in a-Si:H. Japanese Journal of Applied Physics, 1998, 37, 1736-1746.	0.8	0
152	Determination of hot-carrier induced interface state density in polycrystalline silicon thin-film transistors. Journal of Applied Physics, 1998, 84, 2341-2348.	1.1	37
153	Numerical analysis of electrical characteristics of polysilicon thin film transistors fabricated by excimer laser crystallisation. Electronics Letters, 1998, 34, 924.	0.5	28
154	Hot-carrier-induced modifications to the noise performance of polycrystalline silicon thin-film transistors. Applied Physics Letters, 1997, 71, 1216-1218.	1.5	4
155	<title>High-electric-field phenomena in polycrystalline silicon thin film transistors</title>. , 1997, , .		2
156	Excess noise in polysilicon thin film transistors operated in kink regime. Electronics Letters, 1997, 33, 2075.	0.5	2
157	Density of states and photoconductivity light degradation in a-Si:H at different temperatures. Journal of Non-Crystalline Solids, 1996, 198-200, 482-485.	1.5	7
158	Hot-hole-induced degradation in polycrystalline silicon thin-film transistors: experimental and theoretical analysis. IET Circuits, Devices and Systems, 1994, 141, 33.	0.6	5
159	Hot carrier effects in n-channel polycrystalline silicon thin-film transistors: a correlation between off-current and transconductance variations. IEEE Transactions on Electron Devices, 1994, 41, 340-346.	1.6	54
160	Application of the photo induced discharge technique for the investigation of a-Si:H thin-film transistor instability. Journal of Non-Crystalline Solids, 1993, 164-166, 735-738.	1.5	2
161	Study of the defects induced by low-energy (100 eV) hydrogen ions on amorphous silicon dioxide. Applied Physics Letters, 1992, 60, 1564-1566.	1.5	5
162	Instability in hydrogenated amorphous silicon/amorphous silicon dioxide thin-film transistors: Evidence for a predominant effect of charge trapping into the gate insulator. Philosophical Magazine Letters, 1992, 65, 177-182.	0.5	1

#	ARTICLE	IF	CITATIONS
163	Hot carriers effects in polycrystalline silicon thin-film transistors. <i>Microelectronic Engineering</i> , 1992, 19, 109-112.	1.1	3
164	Analysis of short channel effects in poly-Si thin film transistors: A new method. <i>Microelectronic Engineering</i> , 1992, 19, 183-186.	1.1	9
165	Hydrogenated amorphous silicon technology for chemically sensitive thin-film transistors. <i>Sensors and Actuators B: Chemical</i> , 1992, 6, 29-33.	4.0	8
166	Hydrogen effects on a-SiO ₂ : A photoemission study. <i>Journal of Non-Crystalline Solids</i> , 1991, 137-138, 1079-1082.	1.5	3
167	Short-channel effects in 0.2 μ m channel length a-Si:H thin-film transistors fabricated by electron beam lithography. <i>Journal of Non-Crystalline Solids</i> , 1991, 137-138, 1225-1228.	1.5	1
168	Chemically sensitive hydrogenated amorphous silicon thin-film transistors. <i>Journal of Non-Crystalline Solids</i> , 1991, 137-138, 1253-1256.	1.5	2
169	Dispersive charge injection model for hydrogenated amorphous silicon/amorphous silicon dioxide thin-film transistor instability. <i>Applied Physics Letters</i> , 1991, 59, 826-828.	1.5	21
170	Pd-Gate a-Si:H Thin-Film Transistors as Hydrogen Sensors. <i>Japanese Journal of Applied Physics</i> , 1990, 29, L2357-L2359.	0.8	4
171	Source-Drain Metal Contact Effects in Short-Channel a-Si:H Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 1990, 29, L2353-L2356.	0.8	6
172	Theoretical Analysis of a-Si:H Based Multilayer Structure Thin Film Transistors. <i>Japanese Journal of Applied Physics</i> , 1990, 29, 1634-1638.	0.8	2
173	Space-charge photomodulation in metal/insulator/amorphous semiconductor structures (TFTs). <i>IEEE Transactions on Electron Devices</i> , 1989, 36, 2825-2828.	1.6	8
174	Experimental and theoretical evidence of space-charge photomodulation in metal/insulator/amorphous semiconductor structures. <i>Journal of Non-Crystalline Solids</i> , 1989, 114, 378-380.	1.5	6
175	Theory for field-effect mobility enhancement in multilayer structure thin-film transistors. <i>Journal of Non-Crystalline Solids</i> , 1989, 115, 102-104.	1.5	0
176	Transport properties of plasma-deposited amorphous silicon dioxide. <i>Journal of Non-Crystalline Solids</i> , 1989, 115, 123-125.	1.5	7
177	Low voltage operation a-Si:H thin film transistors with very thin PECVD a-SiO ₂ gate dielectric. <i>Journal of Non-Crystalline Solids</i> , 1989, 115, 144-146.	1.5	14
178	Properties of amorphous Si: H films prepared by dual ion beam sputtering. <i>Physica Scripta</i> , 1988, 37, 828-830.	1.2	1
179	Effects of tunneling on a-Si:H Schottky barriers. <i>Journal of Applied Physics</i> , 1987, 62, 3285-3287.	1.1	5
180	a-Si _{1-x} Gex: H alloys for solar cells. <i>Journal of Non-Crystalline Solids</i> , 1987, 97-98, 1075-1078.	1.5	7

#	ARTICLE	IF	CITATIONS
181	Dual-ion-beam sputtering technique for the production of hydrogenated amorphous silicon. Thin Solid Films, 1984, 120, 215-222.	0.8	7